Abstracts

An E-mode GaAs FET power amplifier MMIC for GSM phones

W. Abey, T. Kawai, I. Okamoto, M. Suzuki, C. Khandavalli, W. Kennan, Y. Tateno, M. Nagahara and M. Takikawa. "An E-mode GaAs FET power amplifier MMIC for GSM phones." 1997 MTT-S International Microwave Symposium Digest 3. (1997 Vol. III [MWSYM]): 1315-1318.

An enhancement-mode three stage GaAs FET power MMIC has been developed for single supply portable applications. The MMIC operates from a 4.8 V power supply and provides over 35 dBm output power from 890-915 MHz with more than 35 dB gain and 47% power added efficiency. Power control range is greater than 70 dB. Leakage current is 2 uA.

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